







Features

- Junction passivation optimized design passivated anisotropic rectifier technology
- T_J = 175℃ capability suitable for high reliability and automotive requirement.
- Available in uni-directional polarity only
- Low leakage current
- Low forward voltage drop
- · High surge capability
- AEC-Q101 qualified.

Circuit Diagram



Mechanical Data

- Case: DO-218AB
- Molding compound meets UL 94V-0 flammability rating
- Base P/NHE3-RoHS-compliant, AEC-Q101 qualified
- Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

Maximum Ratings and Thermal Characteristics@TA=25°C unless otherwise specified

Parameter	Symbol	Value	Unit
Peak pulse power dissipation on 10/1000 µs waveform	- P _{PPM}	6600	W
Peak pulse power dissipation on 10/10000 µs waveform	- ГРРМ	5200	W
Power dissipation on infinite heat sink at T_{C} = 25°C	P _D	8.0	w
Typical thermal resistance, junction to case	R _{θJC}	0.9	°C/W
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 to 175	°C

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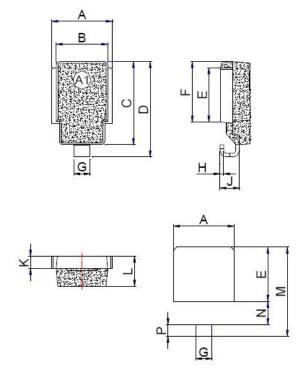




Electrical Characteristics@TA=25° C unless otherwise specified

DEVICE TYPE	REVERSE STAND-OFF VOLTAGE V _{RWM} (V)	VOL V _B	KDOWN TAGE R (V)	TEST CURRENT I _T	CLAMPING VOLTAGE V _C @I _{PP}	PEAK PULSE CURRENT AT 10/1000µs WAVEFORM IPP		E LEAKAGE RRENT I _R
		MIN.	MAX.	MA	V	Α	μA@25°C	μA@175°C
SM8S20CA	20	22.2	24.5	5	32.4	204	5	150
SM8S22CA	22	24.4	26.9	5	35.5	186	5	150
SM8S24CA	24	26.7	29.5	5	38.9	170	5	150
SM8S26CA	26	28.9	31.9	5	42.1	157	5	150
SM8S28CA	28	31.1	34.4	5	45.4	145	5	150
SM8S30CA	30	33.3	36.8	5	48.4	136	5	150
SM8S33CA	33	36.7	40.6	5	53.3	124	5	150
SM8S36CA	36	40.0	44.2	5	58.1	114	5	150

Mechanical Dimensions DO-218AB(Inches/Millimeters)



CVMDOL	Millimeters		Inches		
SYMBOL	Min.	Max.	Min.	Max.	
Α	9.5	10.5	0.374	0.413	
В	8.3	8.7	0.327	0.342	
С	13.3	13.7	0.524	0.539	
D	15.0	16.0	0.592	0.628	
Е	8.5	9.1	0.335	0.358	
F	9.5	10.1	0.374	0.398	
G	2.4	3.0	0.094	0.118	
Н	0.5	0.7	0.020	0.028	
J	2.7	3.7	0.106	0.146	
K	1.9	2.1	0.075	0.083	
L	4.7	5.1	0.185	0.201	
М	14.2	14.8	0.559	0.583	
N	3.5	4.1	0.138	0.161	
Р	1.6	2.2	0.063	0.087	

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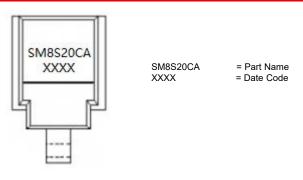


Ordering Information

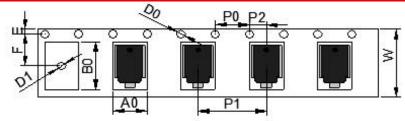
Device	Package	Shipping
SM8S20CA THRU	DO-218AB	750pcs / reel
SM8S36CA		-

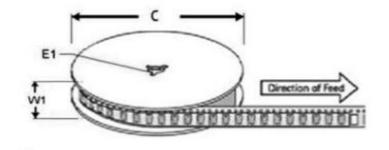
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Carrier Tape Specification DO-218AB





20.20	Dime	nsions	
Ref.	Millimeters	Inches	
A0	10.80 ± 0.3	0.425± 0.012	
В0	16.13 ± 0.3	0.635 ± 0.012	
С	330.0 ± 0.3	13.0 ± 0.012	
D0	1.55 ± 0.2	0.061 ± 0.008	
D1	1.55 ± 0.2	0.061± 0.008	
E	1.75 ± 0.2	0.069 ± 0.008	
E1	13.30 ± 0.2	0.524 ± 0.008	
F	11.50 ± 0.2	0.453 ± 0.008	
P0	4.00 ± 0.2	0.157 ± 0.008	
P1	16.00 ± 0.2	0.630 ± 0.008	
P2	2.00 ± 0.2	0.079 ± 0.00	
W	24.00 ± 0.2	0.945 ± 0.008	
W 1	25.85 ± 0.2	1.018 ± 0.008	







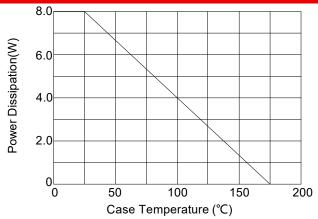


FIG.1: Power Derating Curve

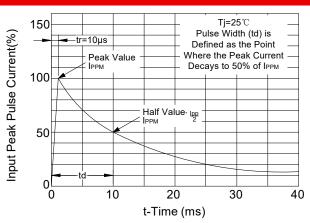


FIG.2: Pulse Waveform

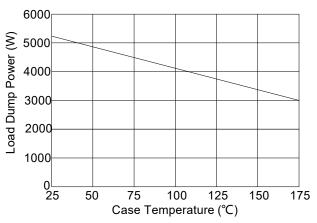


FIG.3: Load Dump Power Characteristics (10ms Exponential Waveform)

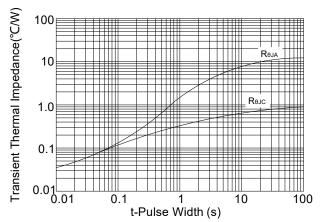


FIG.4: Typical Transient Thermal Impedance





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